

Is Now Part of



# **ON Semiconductor**®

# To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="https://www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="https://www.onsemi.com">Fairchild\_questions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdicii on any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor and its officers, employees, subsidiaries, and lischi charmeded, or individent devices, damages, and reasonable attorney fees arising out or i, directly, any claim of personal injury or death associated with such unintended or unauthorized uspeces that associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the de



SEMICONDUCTOR®

December 2013

## FQP8N80C / FQPF8N80C / FQPF8N80CYDTU **N-Channel QFET® MOSFET**

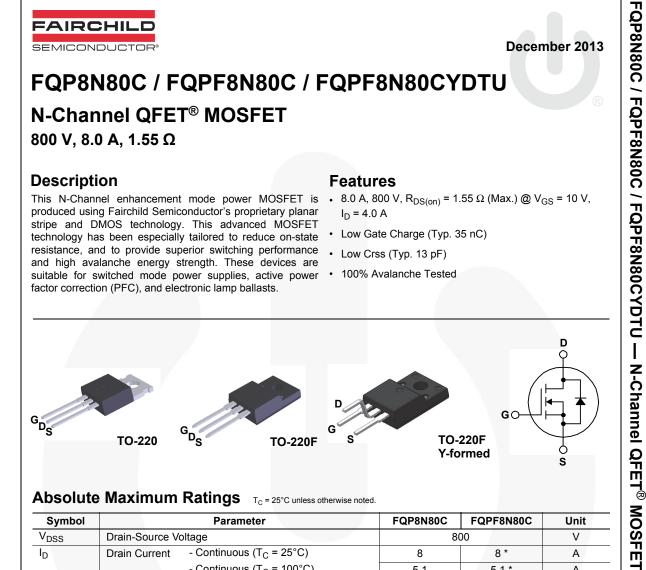
800 V, 8.0 A, 1.55 Ω

### Description

This N-Channel enhancement mode power MOSFET is • 8.0 A, 800 V, R<sub>DS(on)</sub> = 1.55 Ω (Max.) @ V<sub>GS</sub> = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state . Low Gate Charge (Typ. 35 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 13 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

#### Features

- $I_{D} = 4.0 \text{ A}$



#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

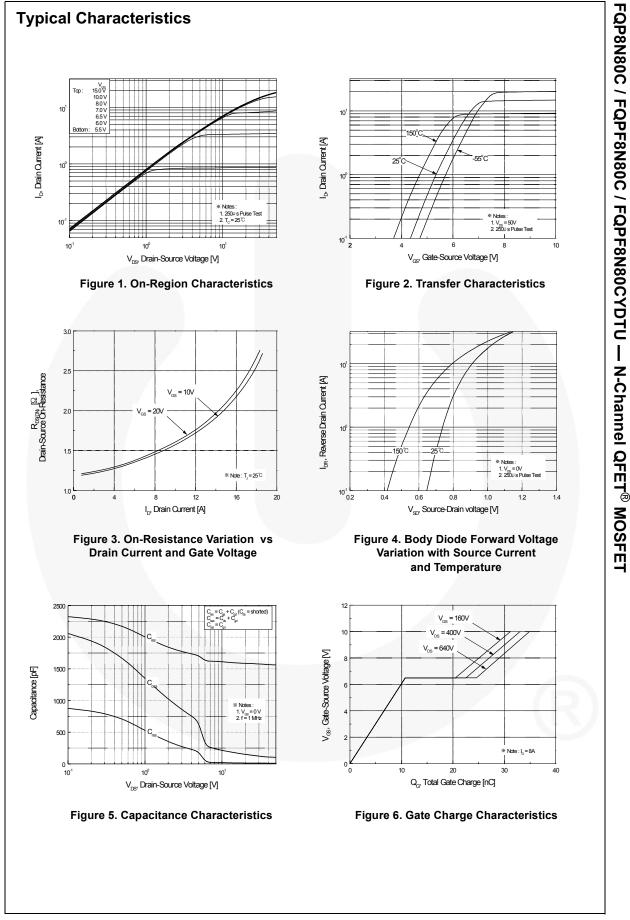
Symbol	Parameter		FQP8N80C	FQPF8N80C	Unit
V <sub>DSS</sub>	Drain-Source Voltage		8	V	
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )		8	8 *	А
	- Continuous (T <sub>C</sub> = 100°C)		5.1	5.1 *	А
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	32	32 *	А
V <sub>GSS</sub>	Gate-Source Voltage	±	V		
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	850		mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)		8	
E <sub>AR</sub>	Repetitive Avalanche Energy (No		17.8		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5		V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		178	59	W
	- Derate above 25°C		1.43	0.48	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150		°C
TI	Maximum lead temperature for soldering,		300		°C
۱L	1/8" from case for 5 seconds	3			

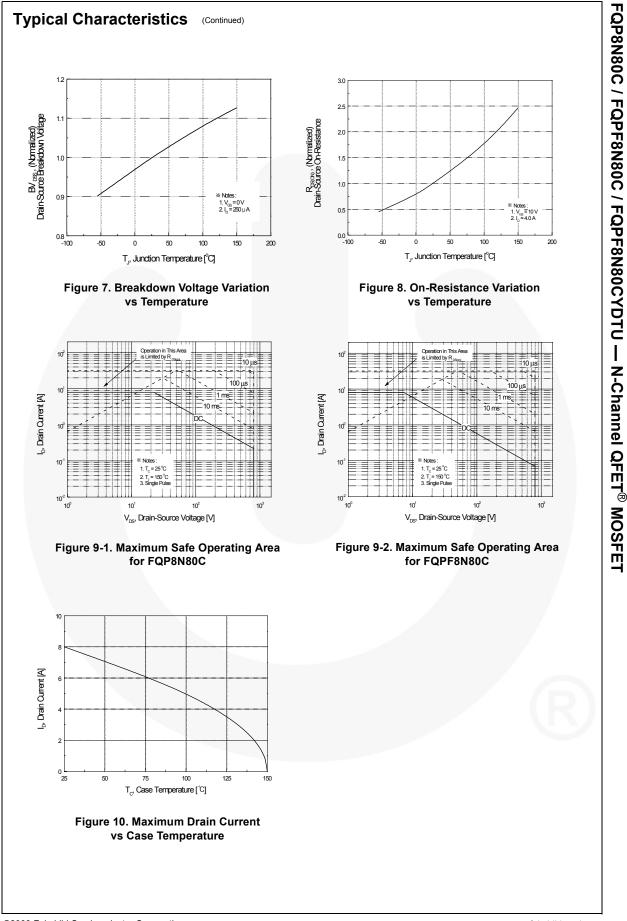
## **Thermal Characteristics**

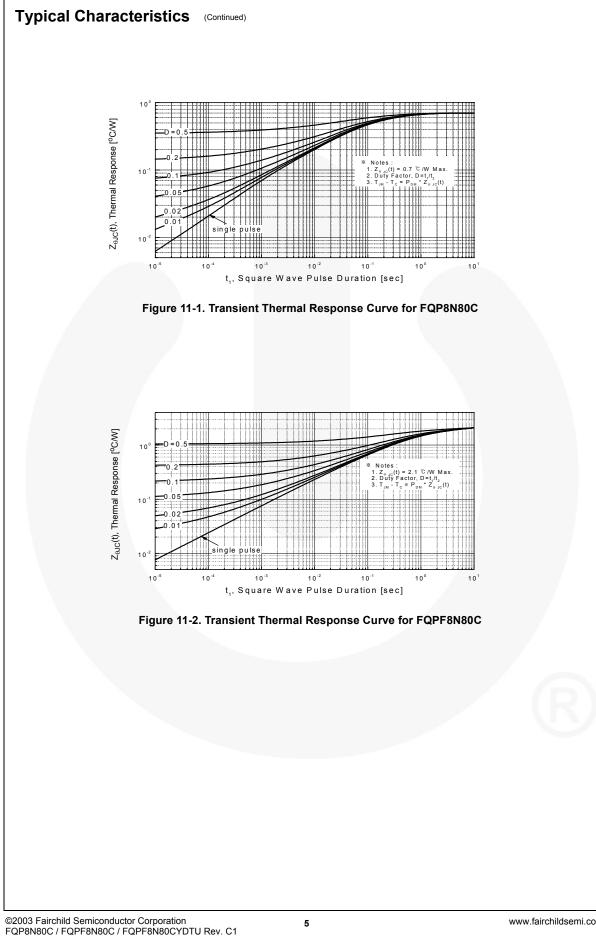
Symbol	Parameter	FQP8N80C	FQPF8N80C	Unit °C/W	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.89	2.66		
R <sub>0CS</sub>	Thermal Resistance, Case-to-Sink Typ, Max.	0.5		°C/W	
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W	

Part Number Top Mark   FQP8N80C FQP8N80C   FQPF8N80C FQPF8N80C   FQPF8N80CYDTU FQPF8N80C		Top Mark	irk Pacl		kage Packing Method Reel S		Size	Tape Width		Quantity	
				220	Tube	N//	4	N/A		50 units	
				220F Tube N/A		4	N/A		50 units 50 units		
			0-220F Tube N/A formed)			A N//					
	cal Char	acteristics Parameter	T <sub>C</sub> = 25°C	C unless oth	erwise noted.		Min.	Тур.	Max.	Unit	
Symbol		T urumeter						196.	max.	Unit	
Off Cha	aracteristi	cs		1			1				
BV <sub>DSS</sub>	Drain-Sour	urce Breakdown Voltage		$V_{GS}$ = 0 V, I <sub>D</sub> = 250 µA			800			V	
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient		$I_D$ = 250 µA, Referenced to 25°C				0.5		V/°C		
DSS	Zero Gate	Voltage Drain Curre	nt	-	800 V, V <sub>GS</sub> = 0 V				10	μΑ	
		Zero Gate Voltage Drain Current		V <sub>DS</sub> = 640 V, T <sub>C</sub> = 125°C					100	μA	
GSSF	-	Leakage Current, F			30 V, V <sub>DS</sub> = 0 V	1			100	nA	
GSSR	Gate-Body	Leakage Current, F	Reverse	V <sub>GS</sub> =	$-30 \text{ V}, \text{ V}_{\text{DS}} = 0 \text{ V}$	_			-100	nA	
On Cha	racteristi	cs									
V <sub>GS(th)</sub>	1	hold Voltage	-	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = 250 μA	-	3.0		5.0	V	
R <sub>DS(on)</sub>	Static Drain				10 V, I <sub>D</sub> = 4 A		-	1.29	1.55	Ω	
9 <sub>FS</sub>	Forward Tr	ansconductance	_	V <sub>DS</sub> =	50 V, I <sub>D</sub> = 4 A	(Note 4)		5.6		S	
Dvnam	ic Charac	teristics					1			1	
C <sub>iss</sub>	Input Capa		_	V				1580	2050	pF	
C <sub>oss</sub>	Output Capacitance		_	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz				135	175	pF	
C <sub>rss</sub>	Reverse Tr	ansfer Capacitance	;	1 - 1.0 WHZ			13	17	pF		
	ing Chara							40	00		
d(on)	Turn-On D	·		$V_{DD} =$	400 V, I <sub>D</sub> = 8 A,			40 110	90	ns	
	Turn-On Ri Turn-Off De			R <sub>G</sub> = 2	5 Ω			65	230 140	ns	
d(off)	Turn-Off Fa	,		ł	(N	ote 4, 5)		70	140	ns	
າ Q <sub>g</sub>	Total Gate				040371 0.4			35	45	nC	
ୁ ପୁ <sub>gs</sub>	Gate-Sour			_	640 V, I <sub>D</sub> = 8 A,			10		nC	
α <sub>gs</sub> Ω <sub>gd</sub>	Gate-Drain	•		V <sub>GS</sub> =		ote 4, 5)		14		nC	
∽yu		ondige			(			17		110	
Drain-S	Source Did	ode Characteri	stics ar	nd Max	timum Ratings						
s	Maximum	Continuous Drain-S	ource Dic	de Forw	ard Current			/	8	Α	
SM	Maximum Pulsed Drain-Source Diode F			Forward Current				1	32	Α	
√ <sub>SD</sub>	Drain-Sour	ce Diode Forward \	/oltage	V <sub>GS</sub> =	0 V, I <sub>S</sub> = 8 A			ł	1.4	V	
rr	Reverse R	ecovery Time		$V_{GS}$ =	0 V, I <sub>S</sub> = 8 A,			690		ns	
Qrr	Reverse R	ecovery Charge		dl⊧ / dt	= 100 A/µs	(Note 4)		8.2		μC	

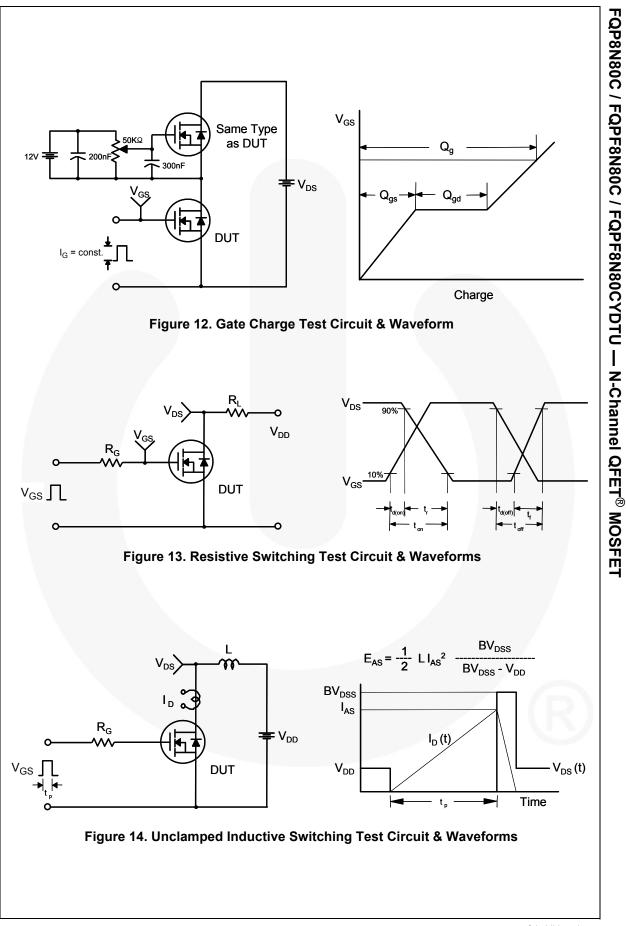
FQP8N80C / FQPF8N80C / FQPF8N80CYDTU — N-Channel QFET® MOSFET

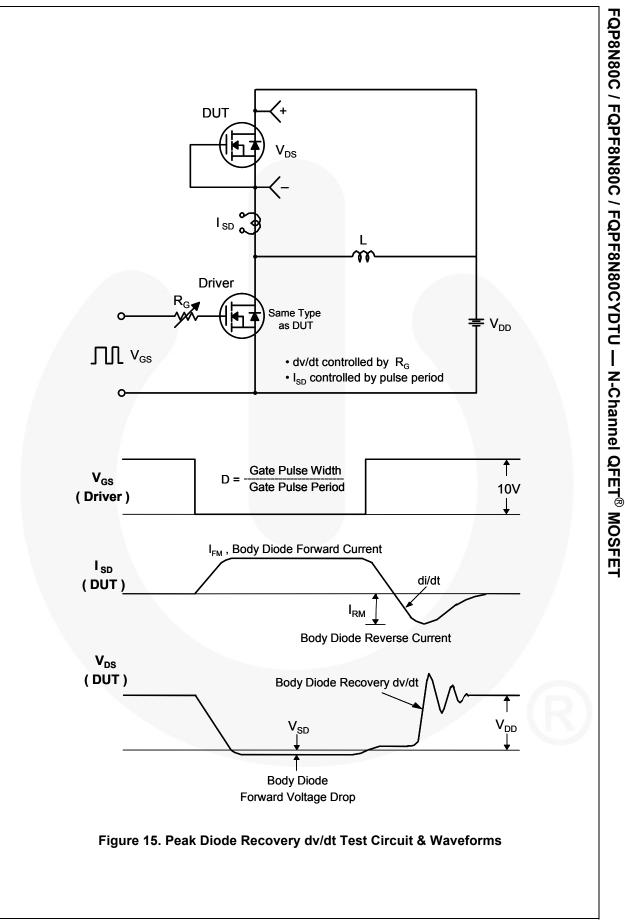


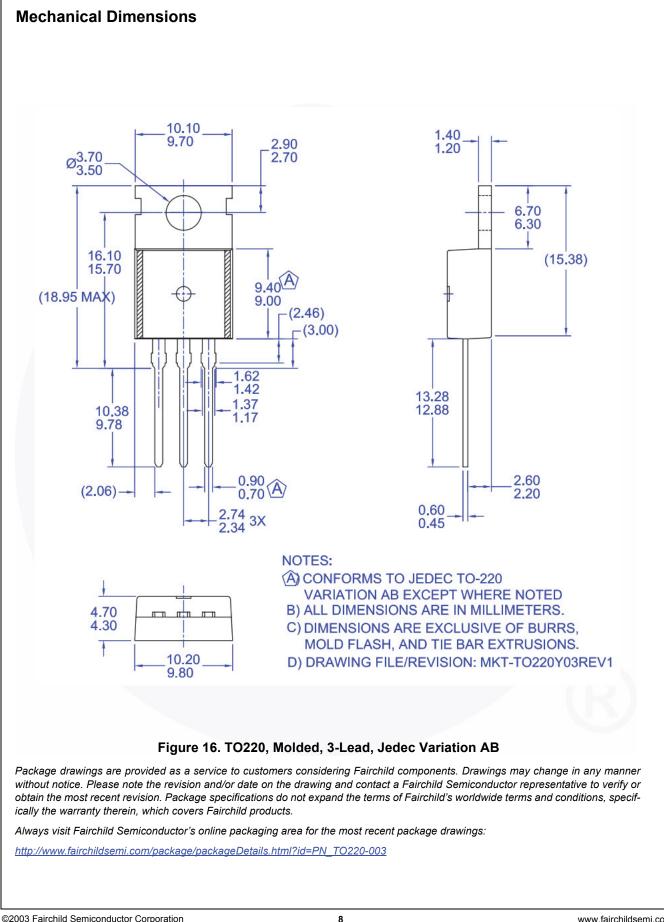




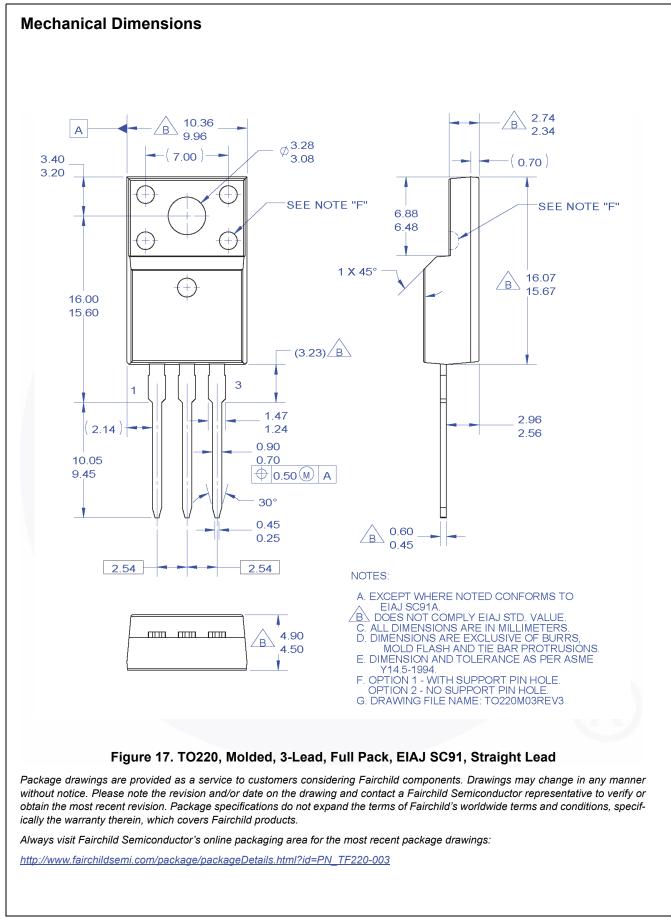
FQP8N80C / FQPF8N80C / FQPF8N80CYDTU — N-Channel QFET<sup>®</sup> MOSFET



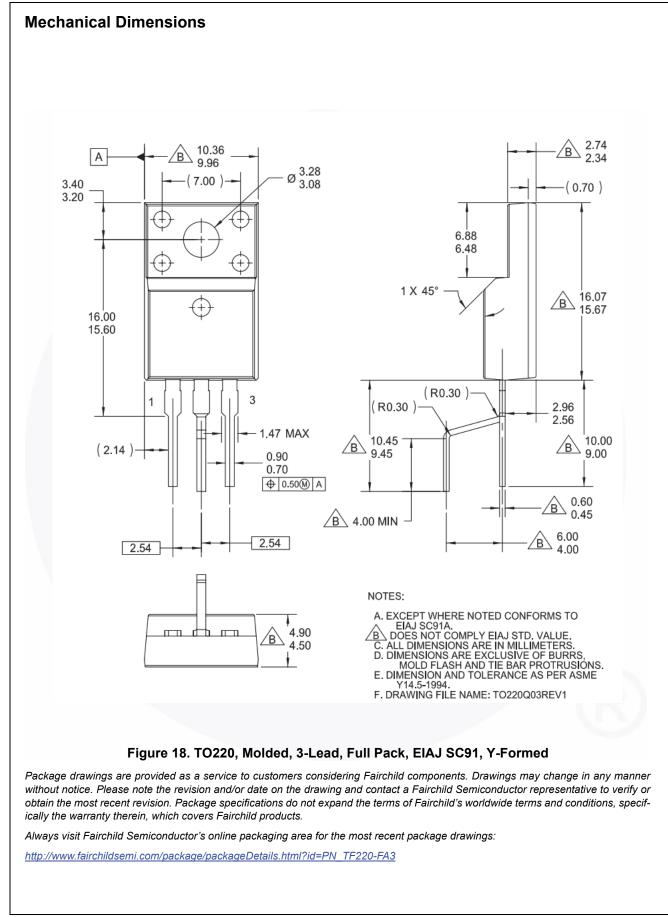




FQP8N80C / FQPF8N80C / FQPF8N80CYDTU Rev. C1



FQP8N80C / FQPF8N80C / FQPF8N80CYDTU — N-Channel QFET<sup>®</sup> MOSFET



FQP8N80C / FQPF8N80C / FQPF8N80CYDTU — N-Channel QFET<sup>®</sup> MOSFET



Obsolete

Downloaded from Arrow.com.

Rev. 166

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

Downloaded from Arrow.com.